EE 466/586 VLSI Design

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Path Optimization using LE



□ Introduce the concept of stage effort

Practical Interpretation



LE for a skewed inverter



Follow board notes
LE will be different for rising and falling cases

Path Optimization using LE



□ Follow board notes

LE of Pseudo-NMOS gates



$$LE = \frac{(C_{in} \times delay)_{gate}}{(C_{in} \times delay)_{inv}} = \frac{(C_{in} \times \Delta t)_{gate}}{(C_{in} \times \Delta t)_{inv}} = \frac{(C_{in} \times C_{out} \Delta V / I)_{gate}}{(C_{in} \times C_{out} \Delta V / I)_{inv}}$$

High fan-in gates

An 8-input AND gate is to be designed to drive a load of 200 fF, with an input capacitance of 20 fF



Pseudo-NMOS Implementation

□ Which one is faster?

Note: The LE of the gates in a logic path, by themselves, do not tell us which configuration is faster. A delay calculation must be performed to make the determination.

Branching Effort

□ Suppose there are one or more branches from a given node



 $total_path_effort = \prod LE \times BE \times FO = (\prod LE \times BE) \times \frac{C_{load}}{C_{in}}$





□ First solve without the side loads

□ Add side load. Remove gates beyond side load but including their loading effects. Solve sub problem.

Combine two solutions.

Side loads

